

## Performance & Technology

Todd C. Mowry  
CS 740

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### Topics:

- Performance measures
- Relating performance measures
- Memory Technology
  - SRAM, DRAM
- Disk Technology

## Performance expressed as a time

### Absolute time measures

- difference between start and finish of an operation
- synonyms: running time, elapsed time, response time, latency, completion time, execution time
- most straightforward performance measure

### Relative (normalized) time measures

- running time normalized to some reference time
- (e.g. time/reference time)

**Guiding principle: Choose performance measures that track running time.**

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## Performance expressed as a rate

Rates are performance measures expressed in units of work per unit time.

### Examples:

- millions of instructions / sec (MIPS)
- millions of floating point instructions / sec (MFLOPS)
- millions of bytes / sec (MBytes/sec)
- millions of bits / sec (Mbits/sec)
- images / sec
- samples / sec
- transactions / sec (TPS)

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## Performance expressed as a rate(cont)

**Key idea: Report rates that track execution time.**

**Example: Suppose we are measuring a program that convolves a stream of images from a video camera.**

### Bad performance measure: MFLOPS

- number of floating point operations depends on the particular convolution algorithm:  $n^2$  matrix-vector product vs  $n \log n$  fast Fourier transform. An FFT with a bad MFLOPS rate may run faster than a matrix-vector product with a good MFLOPS rate.

### Good performance measure: images/sec

- a program that runs faster will convolve more images per second.

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## Performance expressed as a rate(cont)

Fallacy: Peak rates track running time.

Example: the i860 is advertised as having a peak rate of 80 MFLOPS (40 MHz with 2 flops per cycle).

However, the measured performance of some compiled linear algebra kernels (icc -O2) tells a different story:

Kernel	1d fft	sasum	saxpy	sdot	sgemm	sgemv	spvma
MFLOPS	8.5	3.2	6.1	10.3	6.2	15.0	8.1
%peak	11%	4%	7%	13%	8%	19%	10%

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## Relating time to system measures

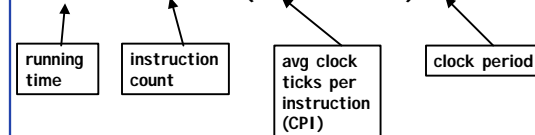
Suppose that for some program we have:

- T seconds running time (the ultimate performance measure)
- C clock ticks, I instructions, P seconds/tick (performance measures of interest to the system designer)

$$T \text{ secs} = C \text{ ticks} \times P \text{ secs/tick}$$

$$= (I \text{ inst}/I \text{ inst}) \times C \text{ ticks} \times P \text{ secs/tick}$$

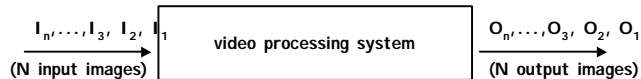
$$T \text{ secs} = I \text{ inst} \times (C \text{ ticks}/I \text{ inst}) \times P \text{ secs/tick}$$



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## Pipeline latency and throughput



Latency (L): time to process an individual image.

Throughput (R): images processed per unit time

One image can be processed by the system at any point in time

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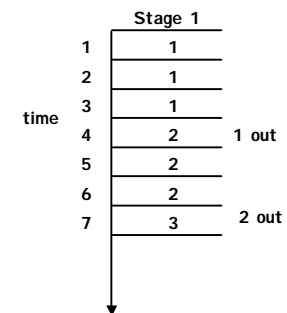
## Video system performance

$$L = 3 \text{ secs/image.}$$

$$R = 1/L = 1/3 \text{ images/sec.}$$

$$T = L + (N-1)1/R$$

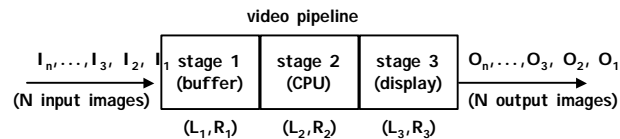
$$= 3N$$



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## Pipelining the video system



One image can be in each stage at any point in time.

$L_i$  = latency of stage  $i$   
 $R_i$  = throughput of stage  $i$

$L = L_1 + L_2 + L_3$   
 $R = \min(R_1, R_2, R_3)$

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## Pipelined video system performance

Suppose:

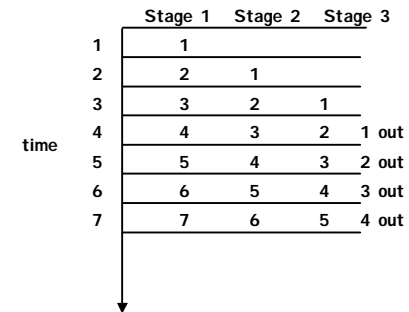
$L_1 = L_2 = L_3 = 1$

Then:

$L = 3$  secs/image.

$R = 1$  image/sec.

$T = L + (N-1)1/R$   
 $= N + 2$



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## Relating time to latency & throughput

In general:

- $T = L + (N-1)/R$

The impact of latency and throughput on running time depends on  $N$ :

- $(N = 1) \Rightarrow (T = L)$
- $(N \gg 1) \Rightarrow (T = N/R)$

To maximize throughput, we should try to maximize the minimum throughput over all stages (i.e., we strive for all stages to have equal throughput).

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## Amdahl's law

You plan to visit a friend in Normandy France and must decide whether it is worth it to take the Concorde SST (\$3,100) or a 747 (\$1,021) from NY to Paris, assuming it will take 4 hours Pgh to NY and 4 hours Paris to Normandy.

	time NY->Paris	total trip time	speedup over 747
747	8.5 hours	16.5 hours	1
SST	3.75 hours	11.75 hours	1.4

Taking the SST (which is 2.2 times faster) speeds up the overall trip by only a factor of 1.4!

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## Amdahl's law (cont)

Old program (unenhanced)

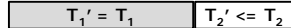


Old time:  $T = T_1 + T_2$

$T_1$  = time that can NOT be enhanced.

$T_2$  = time that can be enhanced.

New program (enhanced)



New time:  $T' = T_1' + T_2'$

$T_2'$  = time after the enhancement.

Speedup:  $S_{\text{overall}} = T / T'$

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## Amdahl's law (cont)

Two key parameters:

$F_{\text{enhanced}} = T_2 / T$  (fraction of original time that can be improved)

$S_{\text{enhanced}} = T_2 / T_2'$  (speedup of enhanced part)

$$\begin{aligned} T' &= T_1' + T_2' = T_1 + T_2' = T(1 - F_{\text{enhanced}}) + T_2' \\ &= T(1 - F_{\text{enhanced}}) + (T_2 / S_{\text{enhanced}}) \quad [\text{by def of } S_{\text{enhanced}}] \\ &= T(1 - F_{\text{enhanced}}) + T(F_{\text{enhanced}} / S_{\text{enhanced}}) \quad [\text{by def of } F_{\text{enhanced}}] \\ &= T((1 - F_{\text{enhanced}}) + F_{\text{enhanced}} / S_{\text{enhanced}}) \end{aligned}$$

Amdahl's Law:

$$S_{\text{overall}} = T / T' = 1 / ((1 - F_{\text{enhanced}}) + F_{\text{enhanced}} / S_{\text{enhanced}})$$

Key idea: Amdahl's law quantifies the general notion of diminishing returns. It applies to any activity, not just computer programs.

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## Amdahl's law (cont)

Trip example: Suppose that for the New York to Paris leg, we now consider the possibility of taking a rocket ship (15 minutes) or a handy rip in the fabric of space-time (0 minutes):

	time NY->Paris	total trip time	speedup over 747
747	8.5 hours	16.5 hours	1
SST	3.75 hours	11.75 hours	1.4
rocket	0.25 hours	8.25 hours	2.0
rip	0.0 hours	8 hours	2.1

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## Amdahl's law (cont)

Useful corollary to Amdahl's law:

$$1 \leq S_{\text{overall}} \leq 1 / (1 - F_{\text{enhanced}})$$

$F_{\text{enhanced}}$	Max $S_{\text{overall}}$	$F_{\text{enhanced}}$	Max $S_{\text{overall}}$
0.0	1	0.9375	16
0.5	2	0.96875	32
0.75	4	0.984375	64
0.875	8	0.9921875	128

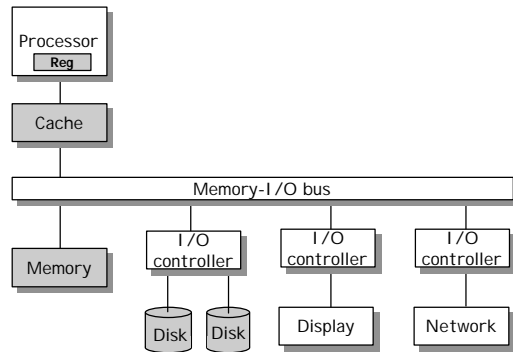
Moral: It is hard to speed up a program.

Moral++ : It is easy to make premature optimizations.

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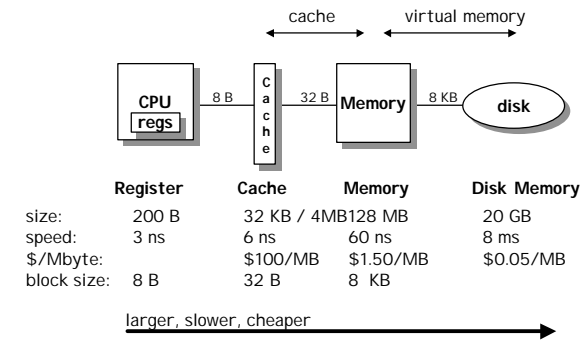
## Computer System



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## Levels in Memory Hierarchy



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## Scaling to 0.1μm

- Semiconductor Industry Association, 1992 Technology Workshop
  - Projected future technology based on past trends

	1992	1995	1998	2001	2004	2007
Feature size:	0.5	0.35	0.25	0.18	0.12	0.10
– Industry is slightly ahead of projection						
DRAM capacity:	16M	64M	256M	1G	4G	16G
– Doubles every 1.5 years						
– Prediction on track						
Chip area (cm <sup>2</sup> ):	2.5	4.0	6.0	8.0	10.0	12.5
– Way off! Chips staying small						

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## Static RAM (SRAM)

### Fast

- ~4 nsec access time

### Persistent

- as long as power is supplied
- no refresh required

### Expensive

- ~\$100/MByte
- 6 transistors/bit

### Stable

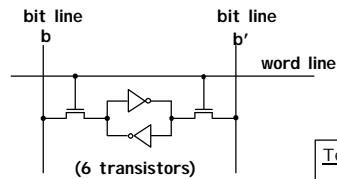
- High immunity to noise and environmental disturbances

### Technology for caches

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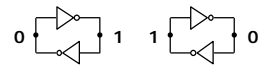
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## Anatomy of an SRAM Cell



(6 transistors)

### Stable Configurations



#### Terminology:

*bit line:* carries data  
*word line:* used for addressing

#### Write:

1. set bit lines to new data value  
•  $b'$  is set to the opposite of  $b$
2. raise word line to "high"  
 $b$  sets cell to new state (may involve flipping relative to old state)

#### Read:

1. set bit lines high
2. set word line high
3. see which bit line goes low

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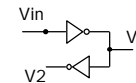
## SRAM Cell Principle

### Inverter Amplifies

- Negative gain
- Slope  $< -1$  in middle
- Saturates at ends

### Inverter Pair Amplifies

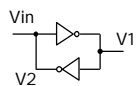
- Positive gain
- Slope  $> 1$  in middle
- Saturates at ends



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## Bistable Element



### Stability

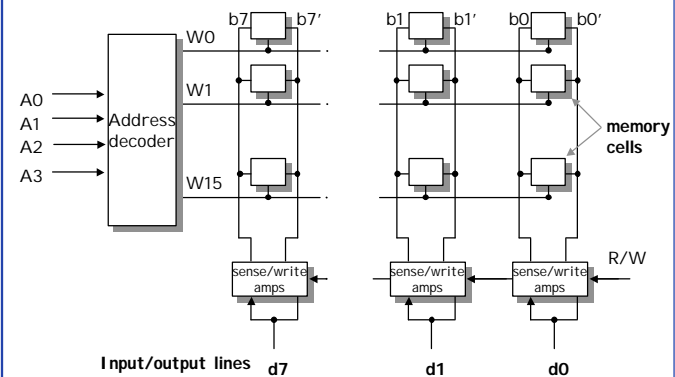
- Require  $V_{in} = V_2$
- Stable at endpoints  
– recover from perturbation
- Metastable in middle  
– Fall out when perturbed

### Ball on Ramp Analogy

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## Example SRAM Configuration (16 x 8)



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## Dynamic RAM (DRAM)

### Slower than SRAM

- access time ~60 nsec

### Nonpersistent

- every row must be accessed every ~1 ms (refreshed)

### Cheaper than SRAM

- ~\$1.50 / MByte
- 1 transistor/bit

### Fragile

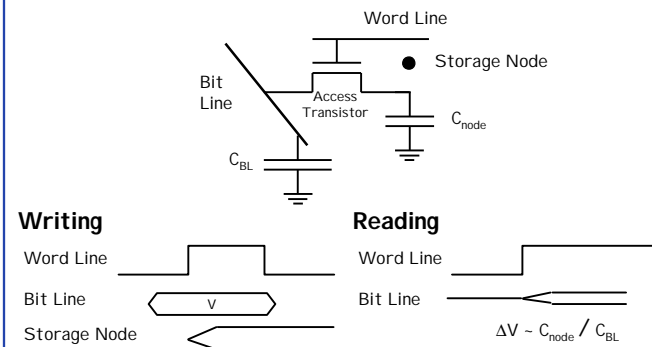
- electrical noise, light, radiation

### Workhorse memory technology

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## Anatomy of a DRAM Cell



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## Addressing Arrays with Bits

### Array Size

- $R$  rows,  $R = 2^r$
- $C$  columns,  $C = 2^c$
- $N = R * C$  bits of memory

### Addressing

- Addresses are  $n$  bits, where  $N = 2^n$
- $\text{row}(\text{address}) = \text{address} / C$   
– leftmost  $r$  bits of address
- $\text{col}(\text{address}) = \text{address} \% C$   
– rightmost bits of address

### Example

- $R = 2$
- $C = 4$
- address = 6

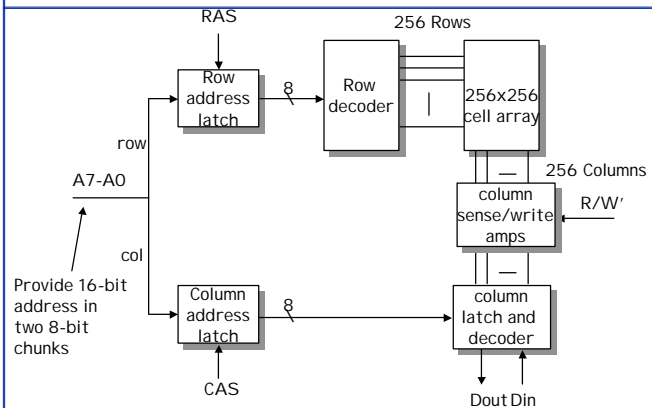
	0	1	2	3
0	000	001	010	011
1	100	101	110	111

row 1      col 2

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## Example 2-Level Decode DRAM (64Kx1)



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## DRAM Operation

### Row Address (~50ns)

- Set Row address on address lines & strobe RAS
- Entire row read & stored in column latches
- Contents of row of memory cells destroyed

### Column Address (~10ns)

- Set Column address on address lines & strobe CAS
- Access selected bit
  - READ: transfer from selected column latch to Dout
  - WRITE: Set selected column latch to Din

### Rewrite (~30ns)

- Write back entire row

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## Observations About DRAMs

### Timing

- Access time (= 60ns) < cycle time (= 90ns)
- Need to rewrite row

### Must Refresh Periodically

- Perform complete memory cycle for each row
- Approximately once every 1ms
- $\sqrt{n}$  cycles
- Handled in background by memory controller

### Inefficient Way to Get a Single Bit

- Effectively read entire row of  $\sqrt{n}$  bits

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## Enhanced Performance DRAMs

### Conventional Access

- Row + Col
- RAS CAS RAS CAS ...

### Page Mode

- Row + Series of columns
- RAS CAS CAS CAS ...
- Gives successive bits

### Other Acronyms

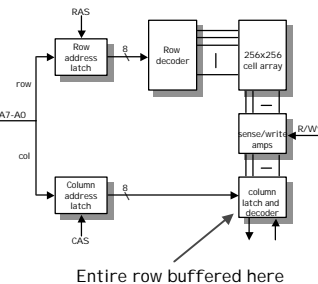
- EDORAM
  - “Extended data output”
- SDRAM
  - “Synchronous DRAM”

### Typical Performance

row access time	col access time	cycle time	page mode cycle time
50ns	10ns	90ns	25ns

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Entire row buffered here

## Video RAM

### Performance Enhanced for Video / Graphics Operations

- Frame buffer to hold graphics image

### Writing

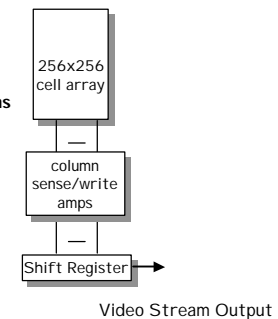
- Random access of bits
- Also supports rectangle fill operations
  - Set all bits in region to 0 or 1

### Reading

- Load entire row into shift register
- Shift out at video rates

### Performance Example

- 1200 X 1800 pixels / frame
- 24 bits / pixel
- 60 frames / second
- 2.8 Gbits / second



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## DRAM Driving Forces

### Capacity

- 4X per generation
  - Square array of cells
- Typical scaling
  - Lithography dimensions 0.7X
    - » Areal density 2X
  - Cell function packing 1.5X
  - Chip area 1.33X
- Scaling challenge
  - Typically  $C_{\text{node}} / C_{\text{BL}} = 0.1\text{--}0.2$
  - Must keep  $C_{\text{node}}$  high as shrink cell size

### Retention Time

- Typically 16–256 ms
- Want higher for low-power applications

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## DRAM Storage Capacitor

### Planar Capacitor

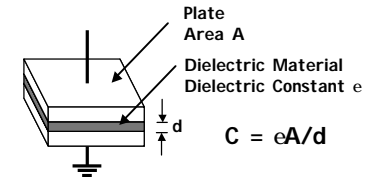
- Up to 1Mb
- C decreases linearly with feature size

### Trench Capacitor

- 4–256 Mb
- Lining of hole in substrate

### Stacked Cell

- > 1Gb
- On top of substrate
- Use high  $\epsilon$  dielectric



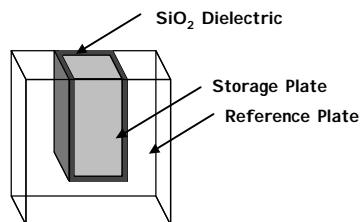
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## Trench Capacitor

### Process

- Etch deep hole in substrate
  - Becomes reference plate
- Grow oxide on walls
  - Dielectric
- Fill with polysilicon plug
  - Tied to storage node



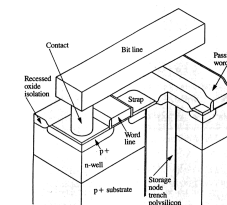
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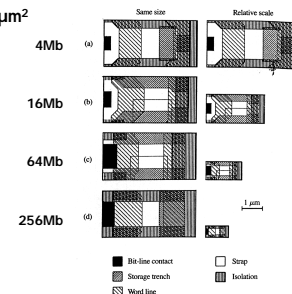
## IBM DRAM Evolution

- IBM J. R&D, Jan/Mar '95
- Evolution from 4 – 256 Mb
- 256 Mb uses cell with area  $0.6 \mu\text{m}^2$

### 4 Mb Cell Structure



### Cell Layouts



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## Mitsubishi Stacked Cell DRAM

- IEDM '95
- Claim suitable for 1 – 4 Gb

Cross Section of 2 Cells

### Technology

- 0.14  $\mu\text{m}$  process
- Synchrotron X-ray source
- 8 nm gate oxide
- 0.29  $\mu\text{m}^2$  cell

(Figure removed)

### Storage Capacitor

- Fabricated on top of everything else
- Rubidium electrodes
- High dielectric insulator
  - 50X higher than  $\text{SiO}_2$
  - 25 nm thick
- Cell capacitance 25 femtofarads

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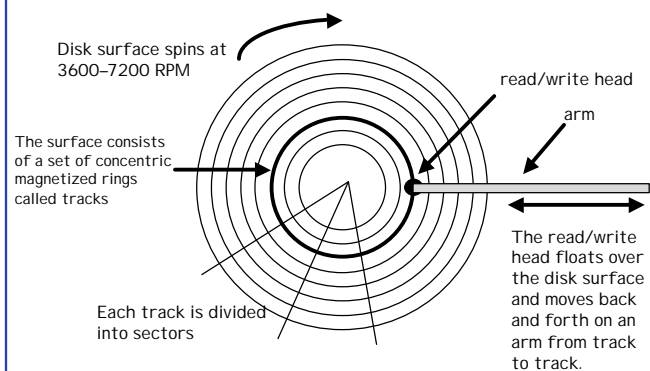
## Mitsubishi DRAM Pictures

(Figures removed)

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## Magnetic Disks



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## Disk Capacity

Parameter	18GB Example
• Number Platters	12
• Surfaces / Platter	2
• Number of tracks	6962
• Number sectors / track	213
• Bytes / sector	512
<b>Total Bytes</b>	<b>18,221,948,928</b>

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## Disk Operation

### Operation

- Read or write complete sector

### Seek

- Position head over proper track
- Typically 6-9ms

### Rotational Latency

- Wait until desired sector passes under head
- Worst case: complete rotation  
10,025 RPM  $\Rightarrow$  6 ms

### Read or Write Bits

- Transfer rate depends on # bits per track and rotational speed
- E.g.,  $213 * 512$  bytes @10,025RPM = 18 MB/sec.
- Modern disks have external transfer rates of up to 80 MB/sec  
– DRAM caches on disk help sustain these higher rates

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## Disk Performance

### Getting First Byte

- Seek + Rotational latency = 7,000 – 19,000  $\mu$ sec

### Getting Successive Bytes

- ~ 0.06  $\mu$ sec each  
– roughly 100,000 times faster than getting the first byte!

### Optimizing Performance:

- Large block transfers are more efficient
- Try to do other things while waiting for first byte  
– switch context to other computing task  
– processor is interrupted when transfer completes

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## Disk / System Interface

### 1. Processor Signals Controller

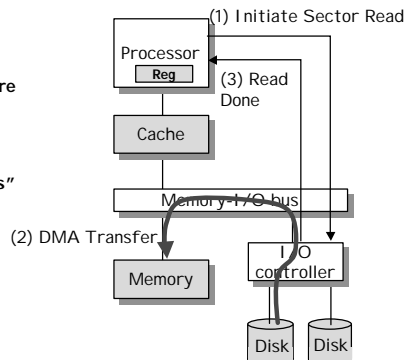
- Read sector X and store starting at memory address Y

### 2. Read Occurs

- "Direct Memory Access" (DMA) transfer
- Under control of I/O controller

### 3. I / O Controller Signals Completion

- Interrupts processor
- Can resume suspended process



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## Magnetic Disk Technology

### Seagate ST-12550N Barracuda 2 Disk

- |                        |         |                       |
|------------------------|---------|-----------------------|
| • Linear density       | 52,187. | bits per inch (BPI)   |
| – Bit spacing          | 0.5     | microns               |
| • Track density        | 3,047.  | tracks per inch (TPI) |
| – Track spacing        | 8.3     | microns               |
| • Total tracks         | 2,707.  | tracks                |
| • Rotational Speed     | 7200.   | RPM                   |
| • Avg Linear Speed     | 86.4    | kilometers / hour     |
| • Head Floating Height | 0.13    | microns               |

### Analogy:

- put the Sears Tower on its side
- fly it around the world, 2.5cm above the ground
- each complete orbit of the earth takes 8 seconds

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## CD Read Only Memory (CDROM)

### Basis

- Optical recording technology developed for audio CDs
  - 74 minutes playing time
  - 44,100 samples / second
  - 2 X 16-bits / sample (Stereo)
    - Raw bit rate = 172 KB / second
- Add extra 288 bytes of error correction for every 2048 bytes of data
  - Cannot tolerate any errors in digital data, whereas OK for audio

### Bit Rate

- $172 * 2048 / (288 + 2048) = 150 \text{ KB / second}$ 
  - For 1X CDROM
  - N X CDROM gives bit rate of  $N * 150$
  - E.g., 12X CDROM gives 1.76 MB / second

### Capacity

- $74 \text{ Minutes} * 150 \text{ KB / second} * 60 \text{ seconds / minute} = 650 \text{ MB}$

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## Storage Trends

### SRAM

metric	1980	1985	1990	1995	2000	2000:1980
\$/MB	19,200	2,900	320	256	100	190
access (ns)	300	150	35	15	2	100

### DRAM

metric	1980	1985	1990	1995	2000	2000:1980
\$/MB	8,000	880	100	30	1.5	5,300
access (ns)	375	200	100	70	60	6
typical size(MB)	0.064	0.256	4	16	64	1,000

### Disk

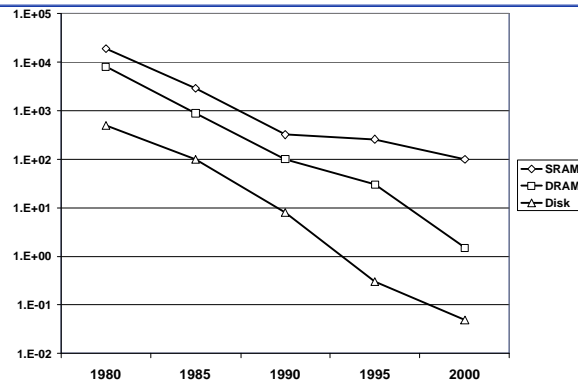
metric	1980	1985	1990	1995	2000	2000:1980
\$/MB	500	100	8	0.30	0.05	10,000
access (ms)	87	75	28	10	8	11
typical size(MB)	1	10	160	1,000	9,000	9,000

(Culled from back issues of Byte and PC Magazine)

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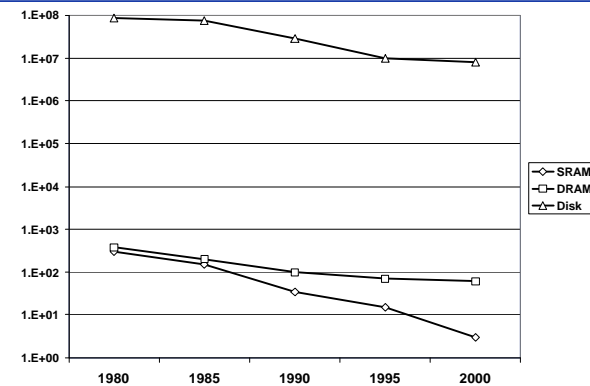
## Storage Price: \$/MByte



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## Storage Access Times (nsec)



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## Processor clock rates

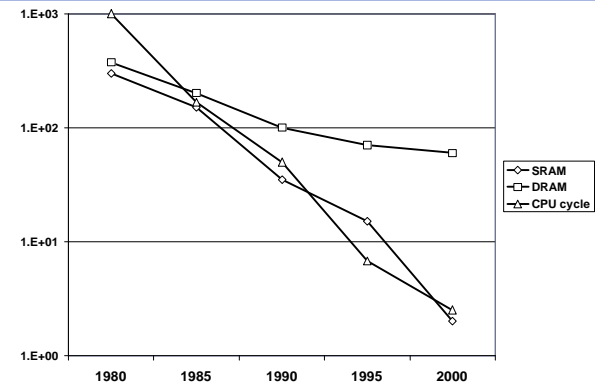
Processors						
metric	1980	1985	1990	1995	2000	2000:1980
typical clock(MHz)	1	6	20	150	600	<b>600</b>
processor	8080	286	386	Pentium P-III		

culled from back issues of Byte and PC Magazine

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## The CPU vs. DRAM Latency Gap (ns)



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## Memory Technology Summary

**Cost and Density Improving at Enormous Rates**

**Speed Lagging Processor Performance**

**Memory Hierarchies Help Narrow the Gap:**

- Small fast SRAMS (cache) at upper levels
- Large slow DRAMS (main memory) at lower levels
- Incredibly large & slow disks to back it all up

**Locality of Reference Makes It All Work**

- Keep most frequently accessed data in fastest memory

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